Microchip

Military

DSP32010

NMOS Digital Signal Processor

FEATURES

- 200 ns instruction cycle
- 144 word on-chip data RAM
- ROM-less version—DSP32010
- 1.5K word on-chip program ROM—DSP320M10
- External memory expansion to a total of 4K words at full speed
- 16-bit instruction/data word
- 32-bit ALU/Accumulator
- 16 x 16-bit multiply in 200 ns
- 0 to 15-bit barrel shifter
- Eight input and eight output channels
- 16-bit bidirectional data bus with a 40 Mbps transfer rate
- Interrupt with a full context save
- Signed two's complement fixed-point arithmetic
- NMOS technology
- Single 5 volt supply
- Extended temperature range:
  —Military (B): -55°C to +110°C

DESCRIPTION

The DSP32010 Digital Signal Processor supports wide range of high-speed or numeric-intensive. This 16/32 bit single-chip microcomputer combines the flexibility of a high-speed controller with the numerical capability of an array processor thereby offering an inexpensive alternative to multichip bit-slice processors. The DSP320 family contains MOS microcomputers capable of executing five million instructions per second. This high throughput is the result of the comprehensive, efficient, and easily programmed instruction set and of the highly pipelined architecture. Special instructions have been incorporated to speed the execution of digital signal processing (DSP) algorithms.

The DSP320 family's unique versatility and power give the design engineer solutions to a variety of complicated applications. In addition, these microcomputers are capable of providing the multiple functions often required for a single application. For example, the DSP320 family can enable an industrial robot to synthesize and recognize speech, sense objects with radar or optical intelligence, and perform mechanical operations through digital servo loop computations.

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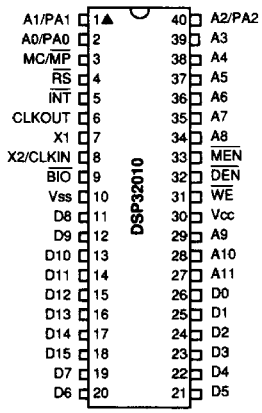
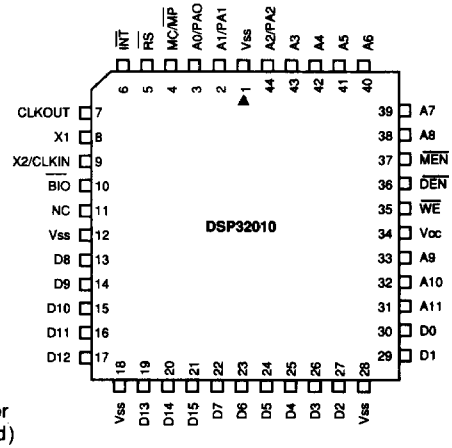
PIN CONFIGURATION
Top View

40 LEAD DIP

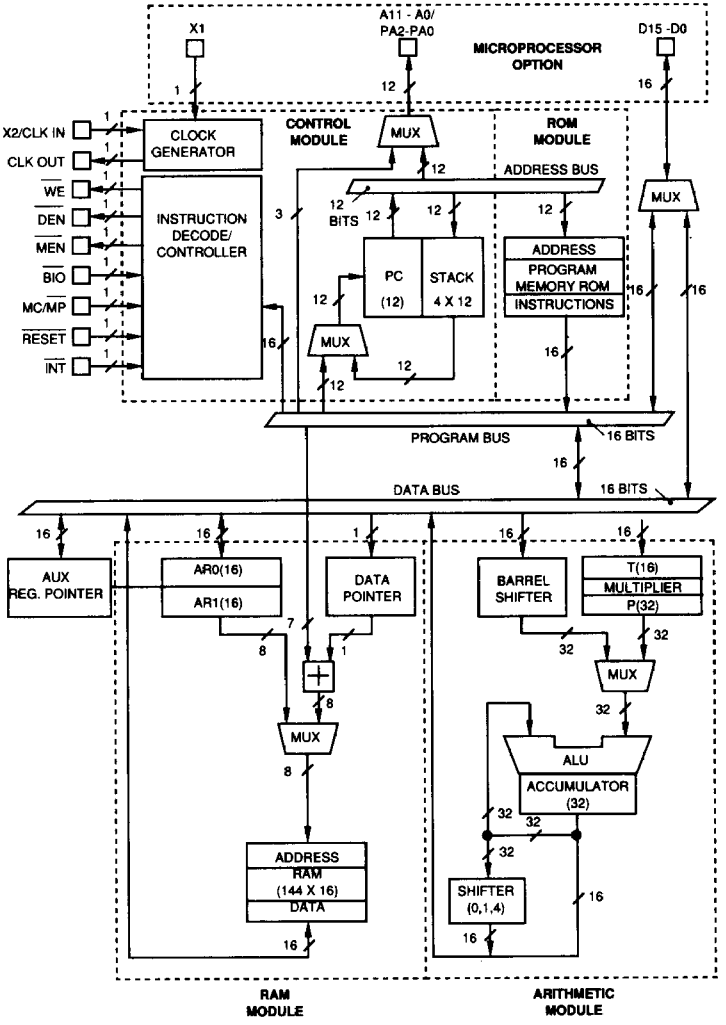


44 PIN LCC



▲ Pin #1 Identifier
NC (Not connected)

DSP32010 BLOCK DIAGRAM



ARCHITECTURE

The DSP320 family utilizes a modified Harvard architecture for speed and flexibility. In a strict Harvard architecture, program and data memory lie in two separate spaces, permitting a full overlap of the instruction fetch and execution. The DSP320 family's modification of the Harvard architecture allows transfers between program and data spaces, thereby increasing the flexibility of the device. This modification permits coefficients stored in program memory to be read into the RAM, eliminating the need for a separate coefficient ROM. It also makes available immediate instructions and subroutines based on computed values.

The DSP32010 utilizes hardware to implement functions that other processors typically perform in software. For example, this device contains a hardware multiplier to perform a multiplication in a single 200 ns cycle. There is also a hardware barrel shifter for shifting data on its way into the ALU. Finally, extra hardware has been included so that auxiliary registers, which provide indirect data RAM addresses, can be configured in an autoincrement/decrement mode for single-cycle manipulation of data tables. This hardware-intensive approach gives the design engineer the type of power previously unavailable on a single chip.

32-bit ALU/accumulator

The DSP32010 contains a 32-bit ALU and accumulator that support double-precision arithmetic. The ALU operates on 16-bit words taken from the data RAM or derived from immediate instructions. Besides the usual arithmetic instructions, the ALU can perform Boolean operations, providing the bit manipulation ability required of a high-speed controller.

Shifters

A barrel shifter is available for left-shifting data 0 to 15 places before it is loaded into, subtracted from, or added to the accumulator. This shifter extends the high-order bit of the data word and zero-fills the low-order bits for two's complement arithmetic A second shifter left-shifts the upper half of the accumulator 0, 1, or 4 places while it is being stored in the data RAM. Both shifters are very useful for scaling and bit extraction.

16 x 16-bit Parallel Multiplier

The DSP32010's multiplier performs a 16 x 16-bit, two's complement multiplication in one 200 ns instruction cycle. The 16-bit T Register temporarily stores the multiplicand; the P Register stores the 32-bit result. Multiplier values either come from the data memory or are derived immediately from the MPYK (multiply immediate) instruction word. The fast on-chip multiplier allows the DSP32010 to perform such fundamental operations as convolution, correlation, and filtering at the rate of 2.56 million samples per second.

Program Memory Expansion

The DSP32010 is equipped with a 1536-word ROM which can be mask-programmed at the factory with a customer's program. It can also execute from an additional 2560 words of off-chip program memory at full speed. this memory expansion capability is especially useful for those situations where a customer has a number of different applications that share the same subroutines. In this case, the common subroutines can be stored on-chip while the application specific code is stored off-chip.

The DSP32010 can operate in either of the following memory modes via the MC/MP pin:

Microcomputer Mode (MC) — Instruction addresses 0-1535 fetched from on-chip ROM. Those with addresses 1536-4095 fetched from off-chip memory at full speed.

Microprocessor Mode ($\overline{MP}$)—Full speed execution from all 4096 off-chip instruction addresses.

The DSP32010 is identical to the DSP320M10, except that the DSP32010 operates only in the microprocessor mode. Henceforth, DSP32010 refers to both versions.

The ability of the DSP32010 to execute at full speed from off-chip memory provides important benefits:

- Easier prototyping and development work than is possible with a device that can address only on-chip ROM
- Purchase of a standard off-the-shelf product rather than a semi-custom mask-programmed device
- Ease of updating code
- Execution from external RAM
- Downloading of code from another microprocessor
- Use of off-chip RAM to expand data storage capability

PIN NOMENCLATURE

Signature	I/O	Definition
A11-A0/-PA2-PA0	OUT	External address bus. I/O port address multiplexed over PA2-PA0.
$\overline{BIO}$	IN	External polling input for bit test and jump operations.
CLKOUT	OUT	System clock output, 1/4 crystal CLKIN frequency.
D15-D0	I/O	16-bit data bus.
$\overline{DEN}$	OUT	Data enable indicates the processor accepting input data on D15-D0.
$\overline{INT}$	IN	Interrupt.
MC/$\overline{MP}$	IN	Memory mode select pin. High selects microcomputer mode. Low selects microprocessor mode.
$\overline{MEN}$	OUT	Memory enable indicates indicates that D15-D0 will accept external memory instruction.
$\overline{RS}$	IN	Reset used to initalize device.
Vcc	IN	Power.
Vss	IN	Ground.
$\overline{WE}$	OUT	Write enable indicates valid data on D15-DO.
X1	IN	Crystal input.
X2/CLKIN	IN	Crystal input or external clock input.

Input/Output

The DSP32010's 16-bit parallel data bus can be utilized to perform I/O functions at burst rates of 40 million bits per second. Available for interfacing to peripheral devices are 128 input and 128 output bits consisting of eight 16-bit multiplexed input ports and eight 16-bit multiplexed output ports. In addition, a polling input for bit test and jump operations ($\overline{BIO}$) and an interrupt pin ($\overline{INT}$) have been incorporated for multi-tasking.

Interrupts and Subroutines

The DSP32010 contains a four-level hardware stack for saving the contents of the program counter during interrupts and subroutine calls. Instructions are available for saving the DSP32010's complete context. The instructions, PUSH stack from accumulator, and POP stack to accumulator permit a level of nesting restricted only by the amount of available RAM. The interrupts used in the DSP32010 are maskable.

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INSTRUCTION SET

The DSP32010's comprehensive instruction set supports both numeric-intensive operations, such as signal processing, and general purpose operations, such as high-speed control. The instruction set, explained in Tables 1 and 2, consists primarily of single-cycle single-word instructions, permitting execution rates of up to five million instructions per second. Only infrequently used branch and I/O instructions are multicycle.

The DSP32010 also contains a number of instructions that shift data as part of an arithmetic operation. These all execute in a single cycle and are very useful for scaling data in parallel with other operations.

Three main addressing modes are available with the DSP32010 instruction set: direct, indirect, and immediate addressing.

Direct Addressing

In direct addressing, seven bits of the instruction word are concatenated with the data page pointer form the data memory address. This implements a paging scheme in which the first page contains 128 words and the second page contains 16 words. In a typical application, infrequently accessed variables, such as those used for servicing an interrupt, are stored on the second page. The instruction format for direct addressing is shown below.

15 14 13 12 11 10 9 8	7	6 5 4 3 2 1 0
OPCODE	0	DMA

Bit 7 = 0 defines direct addressing mode. The opcode is contained in bits 15 through 8. Bits 6 through 0 contain data memory address.

The seven bits of the data memory address (DMA) field can directly address up to 128 words (1 page) of data memory. Use of the data memory page pointer is required to address the full 144 words of data memory.

Direct addressing can be used with all instructions requiring data operands except for the immediate operand instructions.

Indirect Addressing

Indirect addressing forms the data memory from the least significant eight bits of one of two auxiliary registers, AR0 and AR1. The auxiliary register pointer (ARP) selects the current auxiliary register. The auxiliary registers can be automatically incremented or decremented in parallel with the execution of any indirect instruction to permit single-cycle manipulation of data tables. The instruction format for indirect addressing is as follows:

15 14 13 12 11 10 9 8	7	6	5	4	3	2	1	0
OPCODE	1	0	INC	DEC	NAR	0	0	ARP

Bit 7 = 1 defines indirect addressing mode. The opcode is contained in bits 15 through 8. Bits 7 through 0 contain indirect addressing control bits.

Bit 3 and bit 0 control the Auxiliary Register Pointer (ARP). If bit 3 = 0, then the content of bit 0 is loaded into the ARP. If bit 3 = 1, then content of ARP remain unchanged. ARP = 0 defines the contents of AR0 as memory address. ARP = 1 defines the contents of AR1 as memory address.

Bit 5 and bit 4 control the auxiliary registers. If bit 5 = 1, then the ARP defines which auxiliary register is to be incremented by 1. If bit 4 = 1, then the ARP defines which auxiliary register is to be decremented by 1. If bit 5 or bit 4 is zero, then neither auxiliary register is incremented or decremented. Bits 6, 2 and 1 are reserved and should always be programmed to zero.

Indirect addressing can be used with all instructions requiring data operands, except for the immediate operand instructions.

Immediate Addressing

The DSP32010 instruction set contains special "immediate" instructions. These instructions derive data from part of the instruction word rather than from the data RAM. Some very useful immediate instructions are multiply immediate (MPYK), load accumulator immediate (LACK), and load auxiliary register immediate (LARK).

INSTRUCTION SET SUMMARY

TABLE 1 - INSTRUCTION SYMBOLS

Symbol	Meaning
ACC	Accumulator
D	Data memory address field
I	Addressing mode bit
K	Immediate operand field
PA	3-bit port address field
R	1-bit operand field specifying auxiliary register
S	4-bit left-shift code
X	3-bit accumulator left-shift field

TABLE 2 - ACCUMULATOR INSTRUCTIONS

Mnemonic	Description	Number of Cycles	Number of Words	OpCode - Instruction Register 15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ABS	Absolute value of accumulator	1	1	0	1	1	1	1	1	1	1	1	0	0	0	1	0	0	0
ADD	Add to accumulator with shift	1	1	0	0	0	0	←	—	S	→	I	←	—	—	D	—	—	→
ADDH	Add to high-order accumulator bits	1	1	0	1	1	0	0	0	0	0	I	←	—	—	D	—	—	→
ADDS	Add to accumulator with no sign extension	1	1	0	1	1	0	0	0	0	1	I	←	—	—	D	—	—	→
AND	AND with accumulator	1	1	0	1	1	1	1	0	0	1	I	←	—	—	D	—	—	→
LAC	Load accumulator with shift	1	1	0	0	1	0	←	—	S	→	I	←	—	—	D	—	—	→
LACK	Load accumulator immediate	1	1	0	1	1	1	1	1	1	0	←	—	—	—	K	—	—	→
OR	OR with accumulator	1	1	0	1	1	1	1	0	1	0	I	←	—	—	D	—	—	→
SACH	Store high-order accumulator bits with shift	1	1	0	1	0	1	1	←	—	X	→	I	←	—	D	—	—	→
SACL	Store low-order accumulator bits	1	1	0	1	0	1	0	0	0	0	I	←	—	—	D	—	—	→
SUB	Subtract from accumulator with shift	1	1	0	0	0	1	←	—	S	→	I	←	—	—	D	—	—	→
SUBC	Conditional subtract (for divide)	1	1	0	1	1	0	0	1	0	0	I	←	—	—	D	—	—	→
SUBH	Subtract from high-order	1	1	0	1	1	0	0	0	1	0	I	←	—	—	D	—	—	→
SUBS	Subtract from accumulator with no sign extension	1	1	0	1	1	0	0	0	1	1	I	←	—	—	D	—	—	→
XOR	Exclusive OR with accumulator	1	1	0	1	1	1	1	0	0	0	I	←	—	—	D	—	—	→
ZAC	Zero accumulator	1	1	0	1	1	1	1	1	1	1	1	0	0	0	1	0	0	1
ZALH	Zero accumulator and load high-order bits	1	1	0	1	1	0	0	1	0	1	I	←	—	—	D	—	—	→
ZALS	Zero accumulator and load low-order bits with no sign extension	1	1	0	1	1	0	0	1	1	0	I	←	—	—	D	—	—	→

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INSTRUCTION SET SUMMARY (CONT.)

TABLE 2 (CONT.) - AUXILIARY REGISTER AND DATA PAGE POINTER INSTRUCTIONS

Mnemonic	Description	Number of Cycles	Number of Words	OpCode Instruction Register 15 14 13 12 11 10 9 8 7 6 5 4 3 2 1 0
LAR	Load auxiliary register	1	1	0 0 1 1 1 0 0 R I ← D →
LARK	Load auxiliary register immediate	1	1	0 1 1 1 0 0 0 R ← K →
LARP	Load auxiliary register pointer immediate	1	1	0 1 1 0 1 0 0 0 1 0 0 0 0 0 0 K
LDP	Load data memory page pointer	1	1	0 1 1 0 1 1 1 1 I ← D →
LDPK	Load data memory page pointer immediate	1	1	0 1 1 0 1 1 1 0 0 0 0 0 0 0 0 K
MAR	Modify auxiliary register and pointer	1	1	0 1 1 0 1 0 0 0 I ← D →
SAR	Store auxiliary register	1	1	0 0 1 1 0 0 0 R I ← D →

TABLE 2 (CONT.) - BRANCH INSTRUCTIONS

Mnemonic	Description	Number of Cycles	Number of Words	OpCode Instruction Register 15 14 13 12 11 10 9 8 7 6 5 4 3 2 1 0
B	Branch unconditionally	2	2	1 1 1 1 1 0 0 1 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BANZ	Branch on auxiliary register not zero	2	2	1 1 1 1 0 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BGEZ	Branch if accumulator ≥ 0	2	2	1 1 1 1 1 1 0 1 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BGZ	Branch if accumulator > 0	2	2	1 1 1 1 1 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BIOZ	Branch on $\overline{BIO}$ = 0	2	2	1 1 1 1 0 1 1 0 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BLEZ	Branch if accumulator ≤ 0	2	2	1 1 1 1 1 0 1 1 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BLZ	Branch if accumulator < 0	2	2	1 1 1 1 1 0 1 0 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BNZ	Branch if accumulator ≠ 0	2	2	1 1 1 1 1 1 1 0 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BV	Branch on overflow	2	2	1 1 1 1 0 1 0 1 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
BZ	Branch if accumulator = 0	2	2	1 1 1 1 1 1 1 1 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
CALA	Call subroutine from accumulator	2	1	0 1 1 1 1 1 1 1 1 0 0 0 1 1 0 0
CALL	Call subroutine immediately	2	2	1 1 1 1 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 ← BRANCH ADDRESS →
RET	Return from subroutine or interrupt routine	2	1	0 1 1 1 1 1 1 1 1 0 0 0 1 1 0 1

INSTRUCTION SET SUMMARY (CONT.)

TABLE 2 (CONT.) - T REGISTER, P REGISTER, AND MULTIPLY INSTRUCTIONS

Mnemonic	Description	Number of Cycles	Number of Words	OpCode Instruction Register 15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
APAC	Add P register to accumulator	1	1	0	1	1	1	1	1	1	1	1	0	0	0	1	1	1	1
LT	Load T register	1	1	0	1	1	0	1	0	1	0	I	←			D			→
LTA	LTA combines LT and APAC into one instruction	1	1	0	1	1	0	1	1	0	0	I	←			D			→
LTD	LTD combines LT, APAC, and DMOV into one instruction	1	1	0	1	1	0	1	0	1	1	I	←			D			→
MPY	Multiply with T register, store product in P register	1	1	0	1	1	0	1	1	0	1	I	←			D			→
MPYK	Multiply T register with immediate operand; store product in P register	1	1	1	0	0	←						K						→
PAC	Load accumulator from P register	1	1	0	1	1	1	1	1	1	1	1	0	0	0	1	1	1	0

TABLE 2 - (CONT.) - CONTROL INSTRUCTIONS

Mnemonic	Description	Number of Cycles	Number of Words	OpCode Instruction Register 15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
DINT	Disable interrupt	1	1	0	1	1	1	1	1	1	1	1	0	0	0	0	0	0	1
EINT	Enable interrupt	1	1	0	1	1	1	1	1	1	1	1	0	0	0	0	0	1	0
LST	Load status register	1	1	0	1	1	1	1	0	1	1	I	←			D			→
NOP	No operation	1	1	0	1	1	1	1	1	1	1	1	0	0	0	0	0	0	0
POP	POP stack to accumulator	2	1	0	1	1	1	1	1	1	1	1	0	0	1	1	1	0	1
PUSH	PUSH stack from accumulator	2	1	0	1	1	1	1	1	1	1	1	0	0	1	1	1	0	0
ROVM	Reset overflow mode	1	1	0	1	1	1	1	1	1	1	1	0	0	0	1	0	1	1
SOVM	Set overflow mode	1	1	0	1	1	1	1	1	1	1	1	0	0	0	1	0	1	1
SST	Store status register	1	1	0	1	1	1	1	1	0	0	I	←			D			→

TABLE 2 (CONT.) - I/O AND DATA MEMORY OPERATIONS

Mnemonic	Description	Number of Cycles	Number of Words	OpCode Instruction Register 15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
DMOV	Copy contents of data memory	1	1	0	1	1	0	1	0	0	1	I	←			D			→
IN	Input data from port	2	1	0	1	0	0	0	←	PA	→	I	←			D			→
OUT	Output data to port	2	1	0	1	0	0	1	←	PA	→	I	←			D			→
TBLR	Table read from program memory to data RAM	3	1	0	1	1	0	0	1	1	1	I	←			D			→
TBLW	Table write from data RAM to program (external only)	3	1	0	1	1	1	1	1	0	1	I	←			D			→

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DEVELOPMENT SYSTEMS AND SOFTWARE SUPPORT

Software and hardware can be developed using the DSP320C10 macro assembler/linker and the DSP320C10 Simulator for software development and an In-Circuit-Emulator for hardware development.

Microchip Technology offers both the above mentioned software tools. In-Circuit-Emulators are offered by a large number of third party supporters. Please contact your local sales office for a list of third party supporters.

* Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

Maximum Ratings*

Over specified temperature range (unless otherwise noted)*

Supply voltage, Vcc ..... -0.3 V to 7 V
All input voltages ..... -0.3 V to 15 V
Output voltage ..... -0.3 V to 15 V
Continuous power dissipation ..... 1.5 W
Air temperature range above
operating device ..... -55°C to 110°C
Storage temperature range ..... -55°C to 150°C
Junction Temperature (T_J) ..... 165°C
Thermal Resistance (Θ_{JC})
40-Pin Ceramic ... (See Appendix C of Mil-M-38510)
44-Pin LCC ..... 36°/W

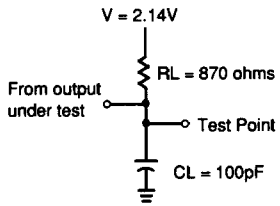
DC CHARACTERISTICS *V_{CC} = 5 V, T_A = 25°C

Characteristics	Min	Nom*	Max	Unit	Conditions
Supply voltage, V_{CC}	4.5	5	5.5	V	
Supply volage, V_{SS}	—	0	—	V	
High-level input voltage, V_{IH}					
All inputs except CLKIN	2	—	—	V	
CLKIN	2.8	—	—	V	
Low-level input voltage, V_{IL} (all inputs)	—	—	0.8	V	
High-level output current, I_{OH} (all outputs)	—	—	-300	µA	
Low-level output current, I_{OL} (all outputs)	—	—	2	mA	
Operating free-air temperature, T_A	-55	—	+110	°C	
High-level output voltage V_{OH}	2.4	3	—	V	I_{OH} = -300 µA
Low-level output voltage, V_{OL}	—	0.3	0.5	V	I_{OL} = 2 mA
Off-state output current, I_{OZ}	—	—	20	µA	V_{CC} = Max, V_O = 2.4 V
	—	—	-20	µA	V_{CC} = Max, V_O = 0.4 V
Input current, I_I	—	—	±50	µA	V_I = V_{SS} to V_{CC}
Supply current, I_{CC}	—	180	275	mA	V_{CC} = Maximum Note 1
	—	—	300	mA	Note 2
Input capacitance, C_I					
Data bus	—	25	—	pF	f = 1MHz, all other pins 0V
All others	—	15	—	pF	f = 1MHz, all other pins 0V
Output capacitance, C_O					
Data bus	—	25	—	pF	f = 1MHz, all other pins 0V
All others	—	10	—	pF	f = 1MHz, all other pins 0V

Note 1: At -55°C
Note 2: At 25°C, 110°C

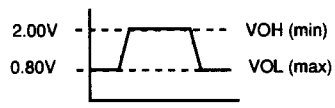
PARAMETER MEASUREMENT INFORMATION

FIGURE 1 - TEST LOAD CIRCUIT



TTL Load Condition

FIGURE 2 - VOLTAGE REFERENCE LEVELS



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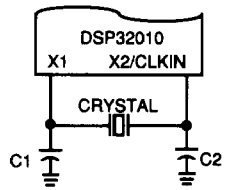
CLOCK

The DSP32010 can use either its internal oscillator or an external frequency source for a clock.

INTERNAL CLOCK OPTION

The internal oscillator is enabled by connecting a crystal across X1 and X2/CLKIN (See Figure 3). The frequency of CLKOUT is one-fourth the crystal fundamental frequency.

FIGURE 3 - INTERNAL CLOCK OPTION



The crystal should be fundamental mode, and parallel resonant, with an effective series resistance of 30 ohms, a power dissipation of 1 mW, and be specified at a load capacitance of 20 pF.

EXTERNAL CLOCK OPTION

An external frequency source can be used by injecting the frequency directly into X2/CLKIN with X1 left unconnected.

The external frequency injected must conform to the specifications listed in the table below.

CLOCK FREQUENCIES

Characteristics	Sym	Min	Nom	Max	Unit	Temperature Range Conditions
Crystal frequency	fx	6.7	—	20	MHz	-55°C to 110°C
C1,C2		—	10	—	pf	—

CLOCK (CONT.)

CLOCK AC CHARACTERISTICS

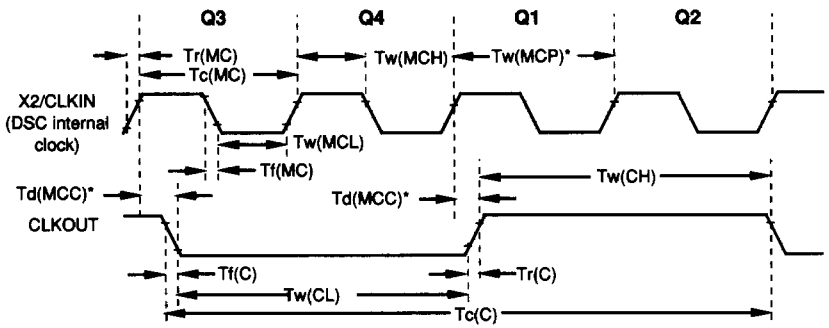
T_A = -55°C to 110°C
V_{CC} = 5 V ± 10%, V_{SS} = 0 V

Timing requirements/Switching Characteristics over Recommended Operating Conditions

Characteristics	Sym	Min	Nom	Max	Unit	Conditions
Master clock cycle time	$T_{C(MC)}$	50	—	150	ns	Note
Rise time master clock input	$T_{R(MC)}$	—	5	10	ns	
Fall time master clock input	$T_{F(MC)}$	—	5	10	ns	
Pulse duration master clock low, $T_{C(MC)}$ = 50ns	$T_{W(MCL)}$	20	—	—	ns	
Pulse duration master clock high, $T_{C(MC)}$ = 50ns	$T_{W(MCH)}$	20	—	—	ns	
Pulse duration master clock	$T_{W(MCP)}$	0.475$T_{C(C)}$	—	0.525$T_{C(C)}$	ns	
CLKOUT cycle time	$T_{C(C)}$	200	—	—	ns	
CLKOUT rise time	$T_{R(C)}$	—	10	—	ns	R_L = 870Ω
CLKOUT fall time	$T_{F(C)}$	—	8	—	ns	C_L = 100pF
Pulse duration, CLKOUT low	$T_{W(CL)}$	—	92	—	ns	See Figure 1
Pulse duration, CLKOUT high	$T_{W(CH)}$	—	90	—	ns	
Delay time to CLKIN↑ to CLKOUT↓ (Note 2)	$T_{D(MCC)}$	10	—	60	ns	

Note:
$T_{C(C)}$ is the cycle time of CLKOUT. i.e., 4*$T_{C(MC)}$ (4 times CLKIN cycle time if an external oscillator is used)

CLOCK TIMING



* $T_{D(MCC)}$ and $T_{W(MCP)}$ are referenced to an intermediate level of 1.5 volts on the CLKIN waveform.
Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

4

MEMORY AND PERIPHERAL INTERFACE TIMING

MEMORY AND PERIPHERAL INTERFACE - AC CHARACTERISTICS
Over recommended operating conditions

Characteristics	Sym	Min	Typ	Max	Unit	Conditions
Delay time CLKOUT↓ to address bus valid (see note)	TD1	10	—	60	ns	RL = 870W, CL = 100 pf, See Figure 1
Delay time CLKOUT↓ to $\overline{MEN}$↓	TD2	1/4Tc(C) -10 ns	—	1/4Tc (C) +15 ns	ns	
Delay time CLKOUT↓ to $\overline{MEN}$↑	TD3	-15	—	15	ns	
Delay time CLKOUT↓ to $\overline{DEN}$↓	TD4	1/4Tc(C) -10 ns	—	1/4Tc (C) +15 ns	ns	
Delay time CLKOUT↓ to $\overline{DEN}$↑	TD5	-15	—	15	ns	
Delay time CLKOUT↓ to $\overline{WE}$↓	TD6	1/2Tc(C) -10 ns	—	1/2Tc(C) +15 ns	ns	
Delay time CLKOUT↓ to $\overline{WE}$↑	TD7	-10	—	15	ns	
Delay time CLKOUT↓ to data bus OUT valid	TD8	—	—	1/4Tc (C) +65 ns	ns	
Time after CLKOUT↓ that data bus starts to be driven	TD9	1/4Tc(C) -10 ns	—	—	ns	
Time after CLKOUT↓ that data bus stops being driven	TD10	—	—	1/4Tc(C) +35 ns*	ns	
Data bus OUT valid after CLKOUT↓	Tv	1/4Tc(C) -10ns	—	—	ns	

Note: Address bus will be valid upon $\overline{WE}$↑, $\overline{DEN}$↑, or $\overline{MEN}$↑.

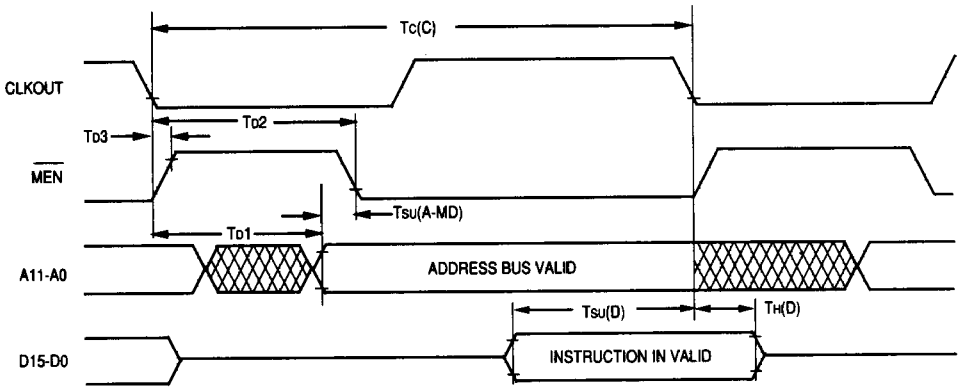
MEMORY AND PERIPHERAL INTERFACE - DC CHARACTERISTICS
Over recommended operating conditions

Characteristics	Sym	Min	Typ	Max	Unit	Conditions
Setup time data bus valid prior to CLKOUT↓	TSU(D)	50	—	—	ns	RL = 870W CL = 100pf See Figure 1
Hold time data bus held valid after CLKOUT↓	TH(D)	0	—	—	ns	
Address bus setup time prior to $\overline{MEN}$↓ or $\overline{DEN}$↓	TSU (A-MD) ns	1/4Tc(C) -45 ns	—	—	ns	

Note: Data may be removed from the data bus upon $\overline{MEN}$↑ or $\overline{DEN}$↑ preceding CLKOUT↓

MEMORY AND PERIPHERAL INTERFACE TIMING (CONT.)

MEMORY READ TIMING DIAGRAM

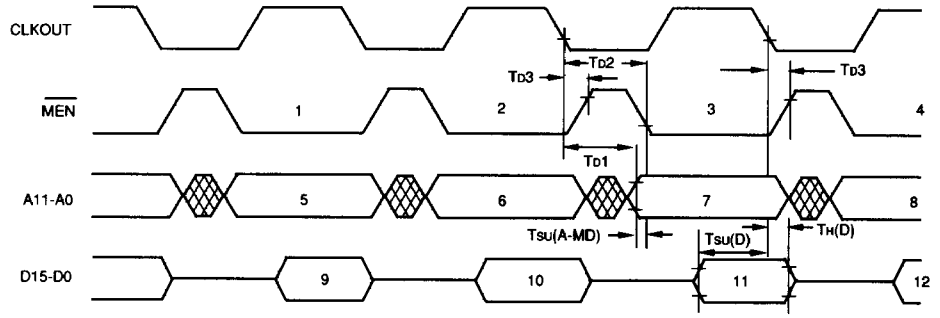


Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

4

INSTRUCTION TIMING DIAGRAMS

TBLR INSTRUCTION TIMING DIAGRAM

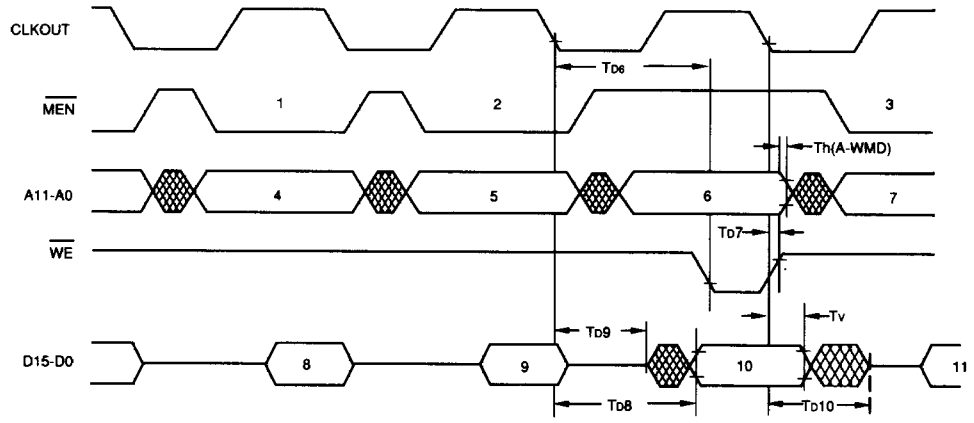


Legend:

1. TBLR INSTRUCTION PREFETCH
2. DUMMY PREFETCH
3. DATA FETCH
4. NEXT INSTRUCTION PREFETCH
5. ADDRESS BUS VALID
6. ADDRESS BUS VALID
7. ADDRESS BUS VALID
8. ADDRESS BUS VALID
9. INSTRUCTION IN VALID
10. INSTRUCTION IN VALID
11. DATA IN VALID
12. INSTRUCTION IN VALID

Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

TBLW INSTRUCTION TIMING DIAGRAM



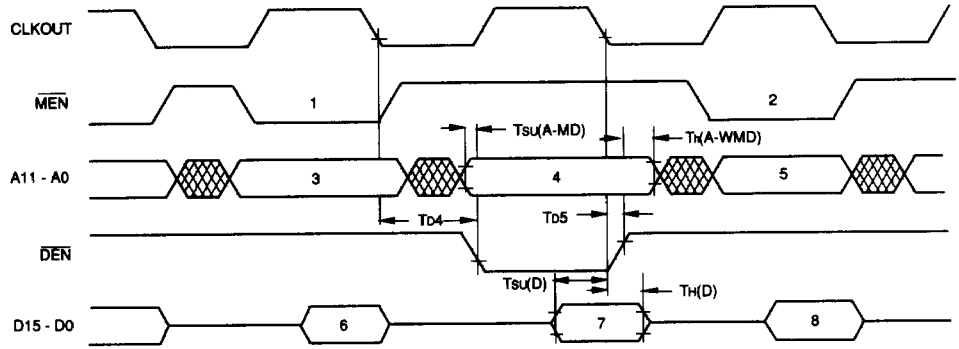
Legend:

1. TBLW INSTRUCTION PREFETCH
2. DUMMY PREFETCH
3. NEXT INSTRUCTION PREFETCH
4. ADDRESS BUS VALID
5. ADDRESS BUS VALID
6. ADDRESS BUS VALID
7. ADDRESS BUS VALID
8. INSTRUCTION IN VALID
9. INSTRUCTION IN VALID
10. DATA OUT VALID
11. INSTRUCTION IN VALID

Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

INSTRUCTION TIMING DIAGRAMS (CONT.)

IN INSTRUCTION TIMING DIAGRAM

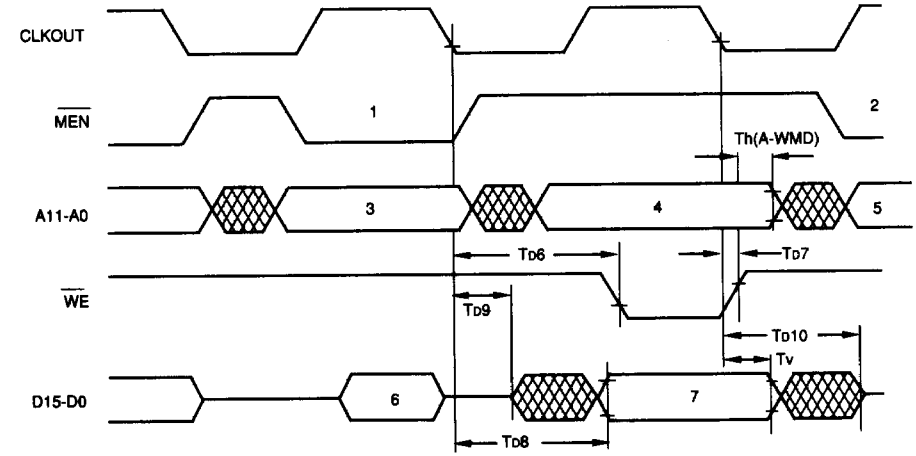


Legend:

1. IN INSTRUCTION PREFETCH
2. NEXT INSTRUCTION PREFETCH
3. ADDRESS BUS VALID
4. PERIPHERAL ADDRESS VALID
5. ADDRESS BUS VALID
6. INSTRUCTION IN VALID
7. DATA IN VALID
8. INSTRUCTION IN VALID

Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

OUT INSTRUCTION TIMING DIAGRAM



Legend:

1. OUT INSTRUCTION PREFETCH
2. NEXT INSTRUCTION PREFETCH
3. ADDRESS BUS VALID
4. PERIPHERAL ADDRESS VALID
5. ADDRESS BUS VALID
6. INSTRUCTION IN VALID
7. DATA OUT VALID

Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

RESET (RS) TIMING

RESET TIMING - AC CHARACTERISTICS

Timing requirements over recommended operating conditions

Characteristics	Sym	Min	Nom	Max	Unit	Conditions
Reset ($\overline{RS}$) setup time prior to CLKOUT. See notes 1-4.	Tsu(R)	50	—	—	ns	
$\overline{RS}$ pulse duration	Tw(R)	5 Tc(C)	—	—	ns	

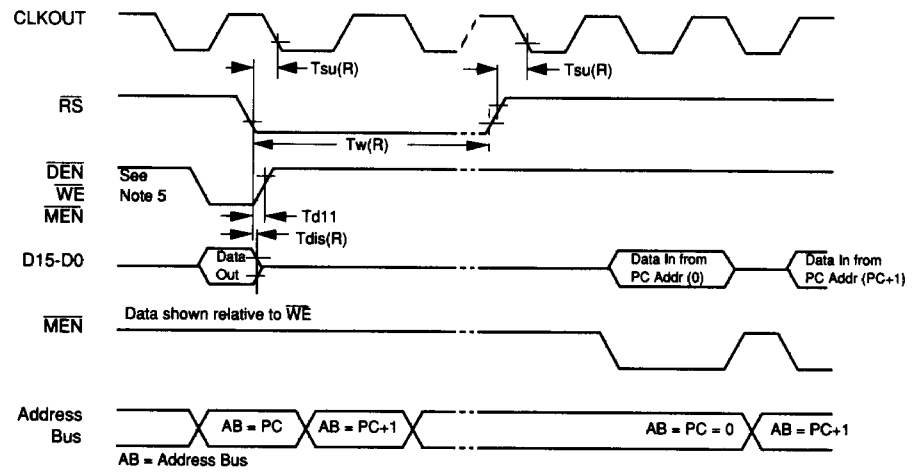
Note: $\overline{RS}$ can occur anytime during a clock cycle. Time given is minimum to ensure synchronous operation.

RESET TIMING - DC CHARACTERISTICS

Timing requirements over recommended operating conditions

Characteristics	Sym	Min	Nom	Max	Unit	Conditions
Delay time $\overline{DEN}\uparrow$, $\overline{WE}\uparrow$, and $\overline{MEN}\uparrow$ from $\overline{RS}\downarrow$	Td11	—	—	.5 Tc(C) + 125	ns	
Data bus disable time after $\overline{RS}$	Tdis(R)	—	—	.25 Tc(C) + 50	ns	See Figure 1

RESET TIMING



Notes:

1. $\overline{RS}$ forces $\overline{DEN}$, $\overline{WE}$, and $\overline{MEN}$ high and tristates data bus DO through D15. AB outputs (and program counter) are synchronously cleared to zero after the next complete CLK cycle from $\overline{RS}\downarrow$.
2. $\overline{RS}$ must be maintained for a minimum of five clock cycles.
3. Resumption of normal program will commence after one complete CLK cycle from $\overline{RS}\uparrow$.
4. Due to the synchronizing action on $\overline{RS}$, time to execute the function can vary dependent upon when $\overline{RS}\uparrow$ or $\overline{RS}\downarrow$ occur in the CLK cycle.
5. Diagram shown is for definition purpose only. $\overline{DEN}$, $\overline{WE}$, and $\overline{MEN}$ are mutually exclusive.
6. Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.
7. During a write cycle, $\overline{RS}$ may produce an invalid write address.

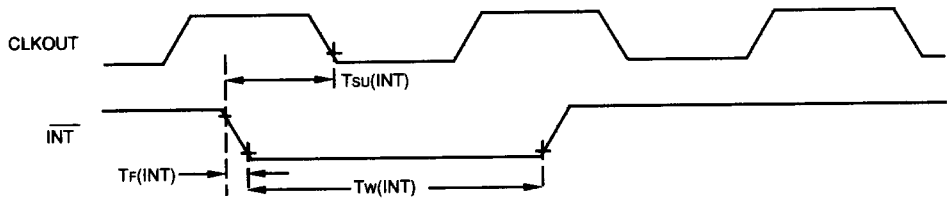
INTERRUPT (INT) TIMING

INTERRUPT TIMING AC CHARACTERISTICS

Timing requirements over recommended operating conditions

Characteristics	Sym	Min	Nom	Max	Unit	Conditions
Fall time $\overline{INT}$	$T_{f(INT)}$	—	—	15	ns	
Pulse duration $\overline{INT}$	$T_{w(INT)}$	$T_{c(C)}$	—	—	ns	
Setup time $\overline{INT}\downarrow$ before CLKOUT$\downarrow$	$T_{su(INT)}$	50	—	—	ns	

INTERRUPT TIMING DIAGRAM



Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

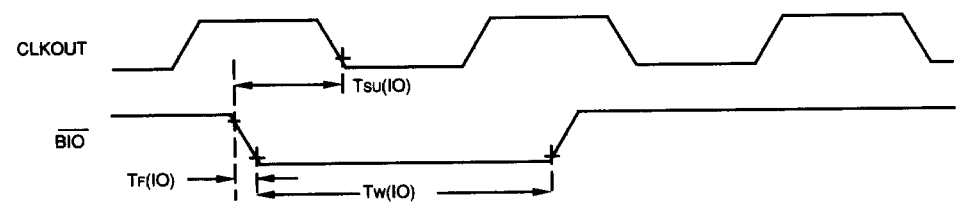
I/O (BIO) TIMING

I/O (BIO) TIMING AC CHARACTERISTICS

Timing requirements over recommended operating conditions

Characteristics	Sym	Min	Nom	Max	Unit	Conditions
Fall time $\overline{BIO}$	$T_{f(IO)}$	—	—	15	ns	
Pulse duration $\overline{BIO}$	$T_{w(IO)}$	$T_{c(C)}$	—	—	ns	
Setup time $\overline{BIO}\downarrow$ before CLKOUT$\downarrow$	$T_{su(IO)}$	50	—	—	ns	

I/O ($\overline{BIO}$) TIMING DIAGRAM

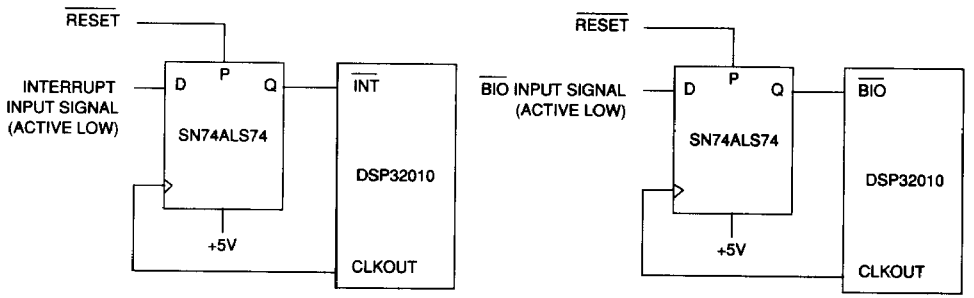


Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

INPUT SYNCHRONIZATION REQUIREMENTS

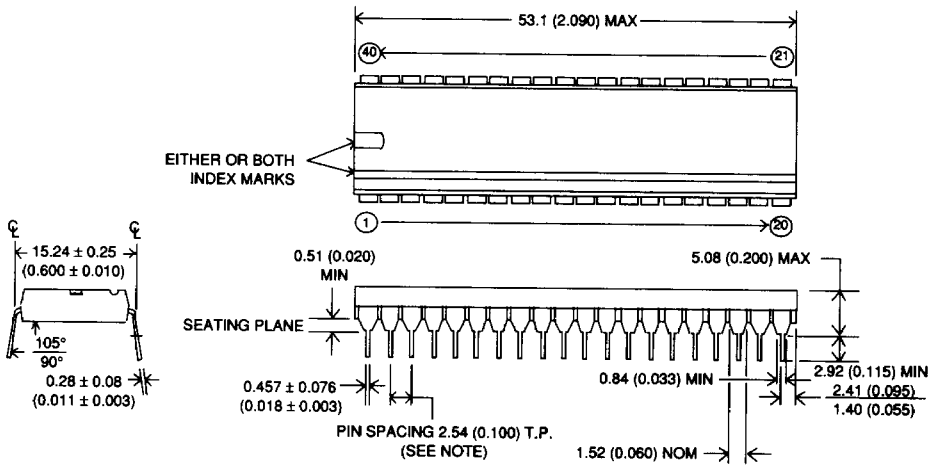
For systems using asynchronous inputs to the $\overline{INT}$ and BIO pins on the DSP32010, the external hardware shown in Figure 4 below is recommended to ensure proper execution of interrupts and the BIOZ instruction. this hardware synchronizes the $\overline{INT}$ and $\overline{BIO}$ input signals with the rising edge of CLKOUT on th DSP32010. The pulse width required for these input signals is Tc(C), which is one DSP32010 clock cycle, plus sufficient setup time for the flip-flop (dependent upon the flip-flop used).

FIGURE 4 - INPUT SYNCHRONIZATION CIRCUITRY



MECHANICANAL DATA

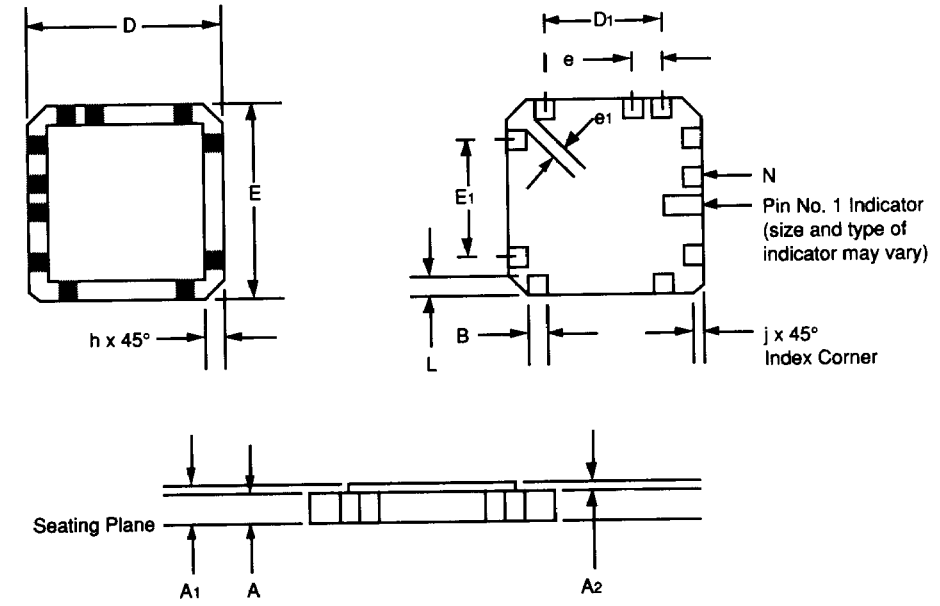
40-PIN CERAMIC DUAL DUAL-IN-LINE PACKAGE



Notes: (1) Each pin centerline is located within 0.254 (0.010) of its true longitudinal position.
(2) All linear dimensions are in millimeters and parenthetically in inches.

MECHANICAL DATA

44-PIN CERAMIC LCC PACKAGE



Package Group: Ceramic Leadless Chip Carrier (LCC)						
	Millimeters			Inches		
Symbol	Min	Max	Notes	Min	Max	Notes
A	1.37	2.082		0.054	0.082	
A_1	1.778	3.048		0.070	0.120	
A_2	0.254	1.143		0.010	0.045	
B	0.584	0.7112	Typical	0.023	0.028	Typical
D	16.256	16.8148		0.640	0.662	
D_1	12.700	12.700	Reference	0.500	0.500	Reference
E	16.256	16.8148		0.640	0.662	
E_1	12.700	12.700	Reference	0.500	0.500	Reference
e	1.270	1.270	Typical	0.050	0.050	Typical
e_1	0.38	–	Typical	0.015	–	Typical
h	1.02	1.02	Reference	0.040	0.040	Reference
j	0.51	0.51	Reference	0.020	0.020	Reference
L	1.143	1.397	Typical	0.045	0.055	Typical
N	44	44		44	44	

4

ORDERING INFORMATION

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers.

PART NUMBERS

84053 - XX - XX

Lead Finish:	A	Solder DIP	Only QA, QC & ZC combinations are supported.
	B	Matte Tin	
	C	Gold	
	X	Any of the above	
Package:	Q	40 Pin Side Braze Ceramic DIL	
	Z	44L Leadless Chip Carrier	
Temperature Range:	1	-55°C to 110°C	
Device:	DESC SMD number for DSP32010 Digital Signal Processor		

Screening per MIL-STD-883C